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**Errata**


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**Erratum: Inelastic scattering in a doped polar semiconductor at finite temperature**  
**[Phys. Rev. B 44, 8319 (1991)]**

Ben Yu-Kuang Hu and S. Das Sarma

Our calculation included only the scattering-out term with the scattering-in term, which is small for our chosen parameters, being left out. It is possible for the scattering-in term to be quantitatively significant for reasonable values of density and temperature, as shown in Ref. 1. We implied that our calculation of the scattering-out rates for electrons in doped polar semiconductors was applicable to the decay of a nonequilibrium distribution of electrons injected into the system. However, the decay of the distribution function is in fact determined by both the scattering-out *and* scattering-in rates. Details and a corrected figure are given in Ref. 1.

<sup>1</sup>B. A. Sanborn, Ben Yu-Kuang Hu, and S. Das Sarma, this issue, Phys. Rev. B 49, 7767 (1994).

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**Erratum: Magnetic-field-induced free electron and hole recombination**  
**in semimetallic  $\text{Al}_x\text{Ga}_{1-x}\text{Sb}/\text{InAs}$  quantum wells**  
**[Phys. Rev. B 48, 9118 (1993)]**

Ikai Lo, W. C. Mitchel, and J.-P. Cheng

Figure 4 was inadvertently omitted from the above paper and is reproduced here.

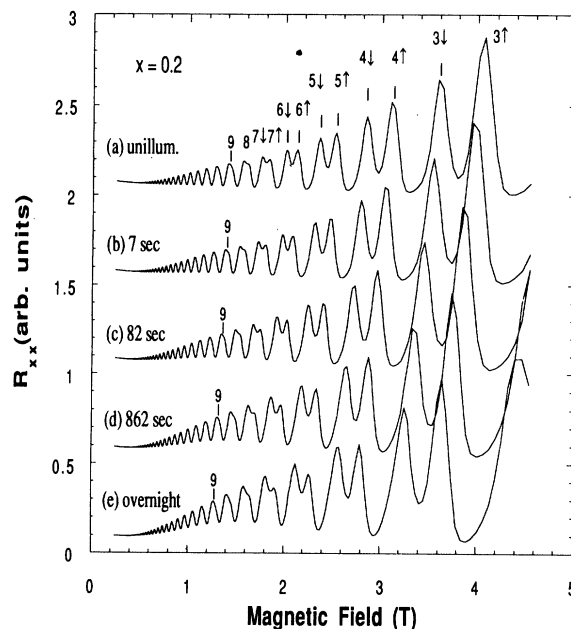


FIG. 4. The low-field magnetoresistance  $R_{xx}$  measurements for the second  $x=0.2$  sample, which has a higher electron concentration.